

EH1445SJETS-6.720M TR



ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) HCMOS/TTL (CMOS) 5.0Vdc J-Lead 9.8mm x 14.0mm Plastic Surface Mount (SMD) 6.720MHz ± 50 ppm -40°C to $+85^{\circ}\text{C}$

ELECTRICAL SPECIFICATIONS

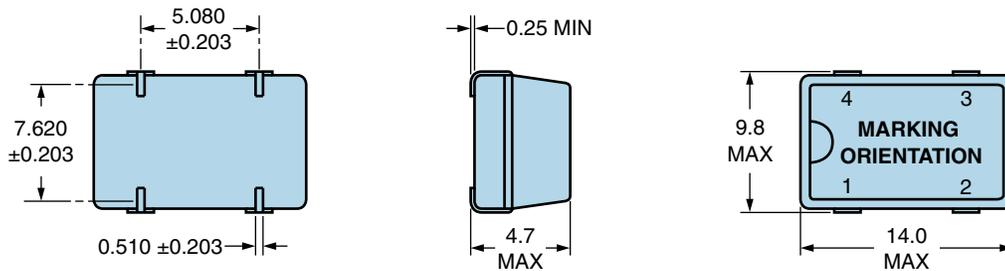
| | |
|---------------------------------------|--|
| Nominal Frequency | 6.720MHz |
| Frequency Tolerance/Stability | ± 50 ppm Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C , Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°C , Shock, and Vibration) |
| Aging at 25°C | ± 5 ppm/year Maximum |
| Operating Temperature Range | -40°C to $+85^{\circ}\text{C}$ |
| Supply Voltage | 5.0Vdc $\pm 10\%$ |
| Input Current | 50mA Maximum (No Load) |
| Output Voltage Logic High (Voh) | 2.4Vdc Minimum with TTL Load, Vdd-0.4Vdc Minimum with HCMOS Load, IOH = -16mA |
| Output Voltage Logic Low (Vol) | 0.4Vdc Maximum with TTL Load, 0.5Vdc Maximum with HCMOS Load, IOL = +16mA |
| Rise/Fall Time | 6nSec Maximum (Measured at 0.8Vdc to 2.0Vdc with TTL Load; Measured at 20% to 80% of waveform with HCMOS Load) |
| Duty Cycle | 50 ± 10 (%) (Measured at 1.4Vdc with TTL Load or at 50% of waveform with HCMOS Load) |
| Load Drive Capability | 10TTL Load or 50pF HCMOS Load Maximum |
| Output Logic Type | CMOS |
| Pin 1 Connection | Tri-State (Disabled Output: High Impedance) |
| Tri-State Input Voltage (Vih and Vil) | +2.2Vdc Minimum to enable output, +0.8Vdc Maximum to disable output (High Impedance), No Connect to enable output. |
| Absolute Clock Jitter | ± 250 pSec Maximum, ± 100 pSec Typical |
| One Sigma Clock Period Jitter | ± 50 pSec Maximum, ± 30 pSec Typical |
| Start Up Time | 10mSec Maximum |
| Storage Temperature Range | -55°C to $+125^{\circ}\text{C}$ |

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

| | |
|------------------------------|---|
| ESD Susceptibility | MIL-STD-883, Method 3015, Class 1, HBM: 1500V |
| Fine Leak Test | MIL-STD-883, Method 1014, Condition A (Internal Crystal Only) |
| Flammability | UL94-V0 |
| Gross Leak Test | MIL-STD-883, Method 1014, Condition C (Internal Crystal Only) |
| Mechanical Shock | MIL-STD-202, Method 213, Condition C |
| Moisture Resistance | MIL-STD-883, Method 1004 |
| Resistance to Soldering Heat | MIL-STD-202, Method 210, Condition K |
| Resistance to Solvents | MIL-STD-202, Method 215 |
| Solderability | MIL-STD-883, Method 2003 |
| Temperature Cycling | MIL-STD-883, Method 1010, Condition B |
| Vibration | MIL-STD-883, Method 2007, Condition A |

EH1445SJETS-6.720M TR

MECHANICAL DIMENSIONS (all dimensions in millimeters)

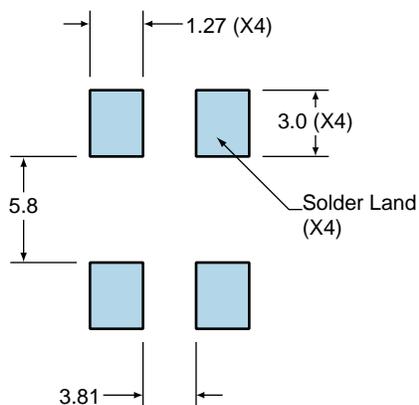


| PIN | CONNECTION |
|-----|----------------------------|
| 1 | Tri-State (High Impedance) |
| 2 | Ground |
| 3 | Output |
| 4 | Supply Voltage |

| LINE | MARKING |
|------|--|
| 1 | ECLIPTEK |
| 2 | 6.7200M |
| 3 | XXXXX XXXXX=Ecliptek Manufacturing Identifier |

Suggested Solder Pad Layout

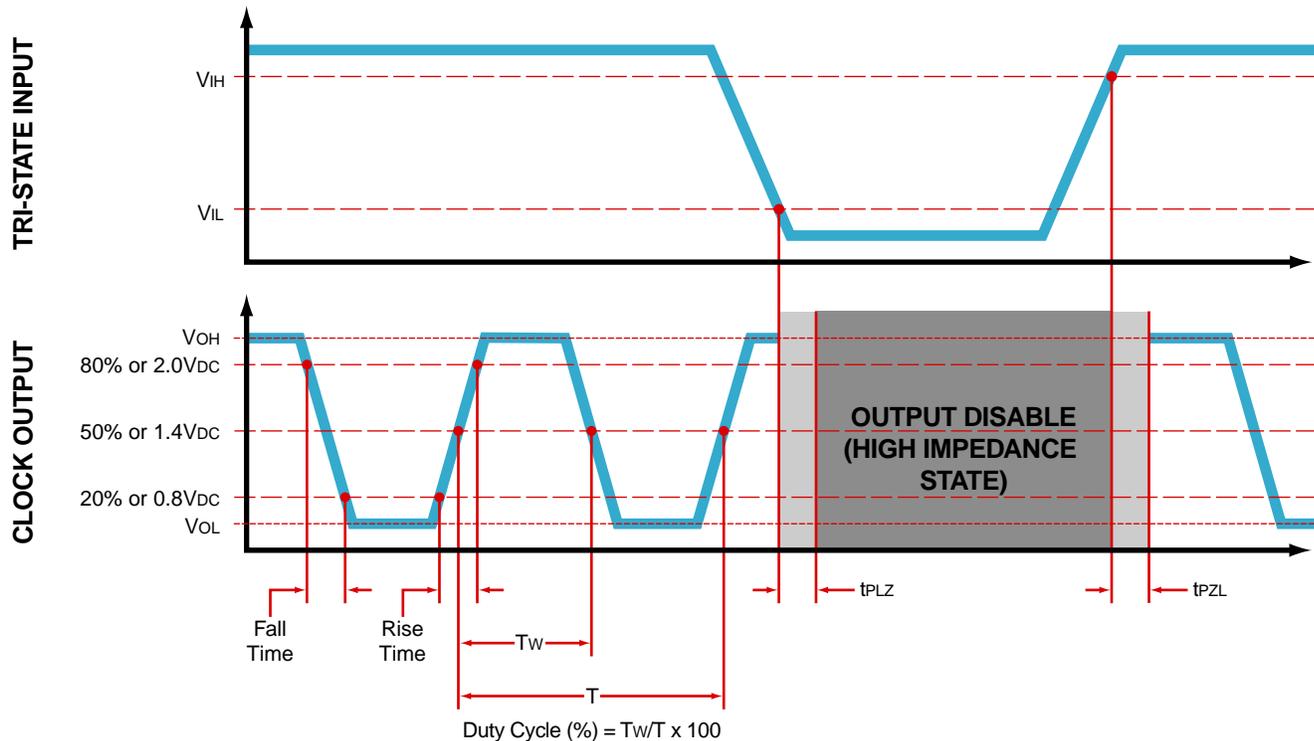
All Dimensions in Millimeters



All Tolerances are ±0.1

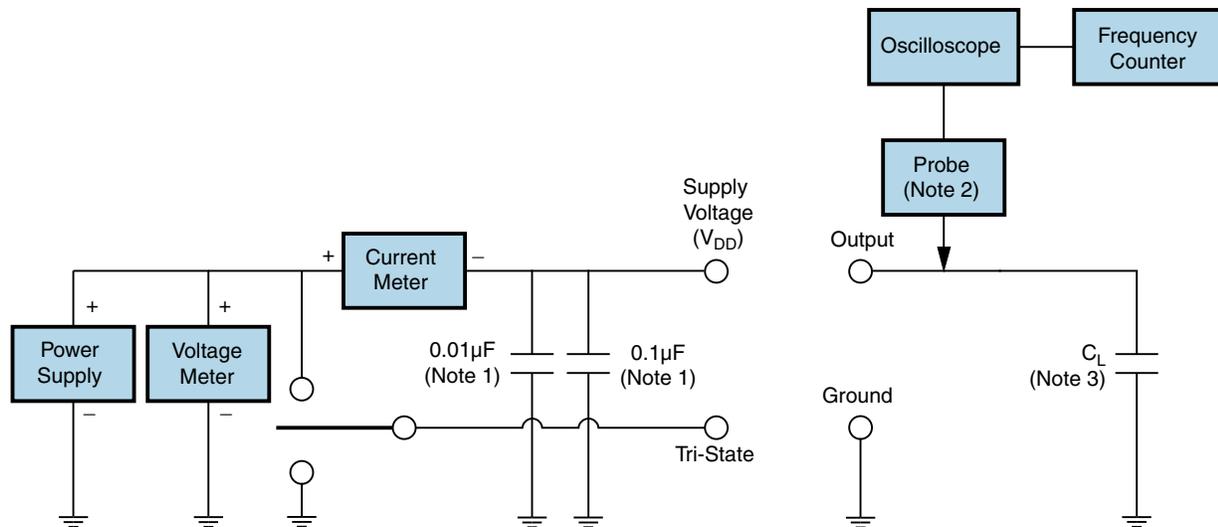
EH1445SJETS-6.720M TR

OUTPUT WAVEFORM & TIMING DIAGRAM



EH1445SJETS-6.720M TR

Test Circuit for CMOS Output



Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

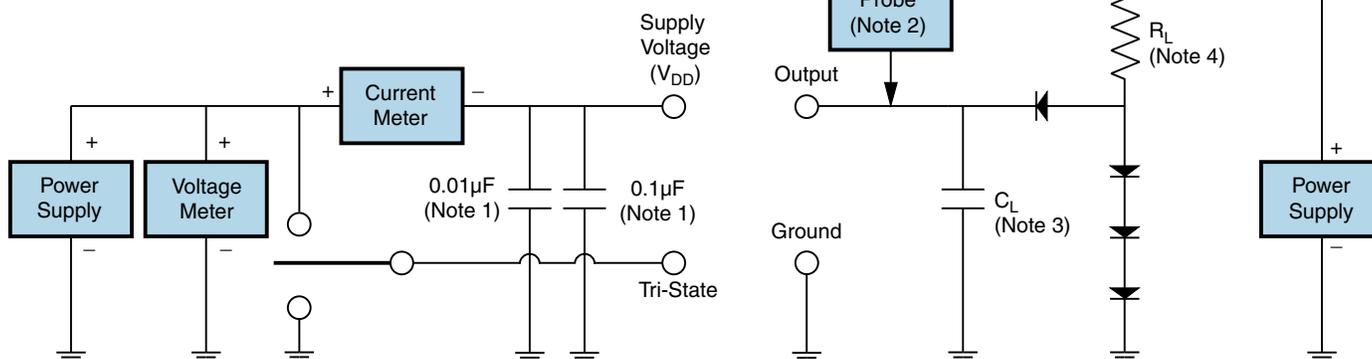
Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

EH1445SJETS-6.720M TR

Test Circuit for TTL Output

| Output Load Drive Capability | R_L Value (Ohms) | C_L Value (pF) |
|------------------------------|--------------------|------------------|
| 10TTL | 390 | 15 |
| 5TTL | 780 | 15 |

Table 1: R_L Resistance Value and C_L Capacitance Value Vs. Output Load Drive Capability



Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value C_L includes sum of all probe and fixture capacitance.

Note 4: Resistance value R_L is shown in Table 1. See applicable specification sheet for 'Load Drive Capability'.

Note 5: All diodes are MMBD7000, MMBD914, or equivalent.

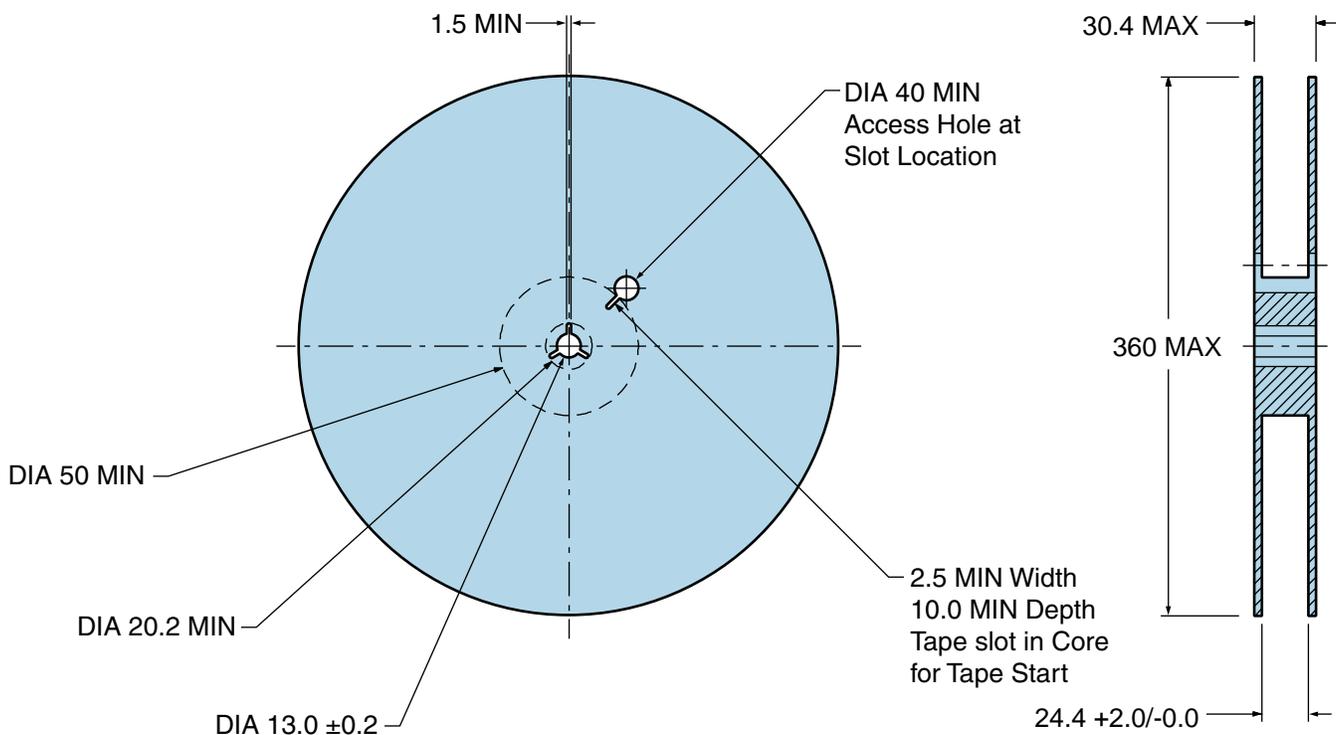
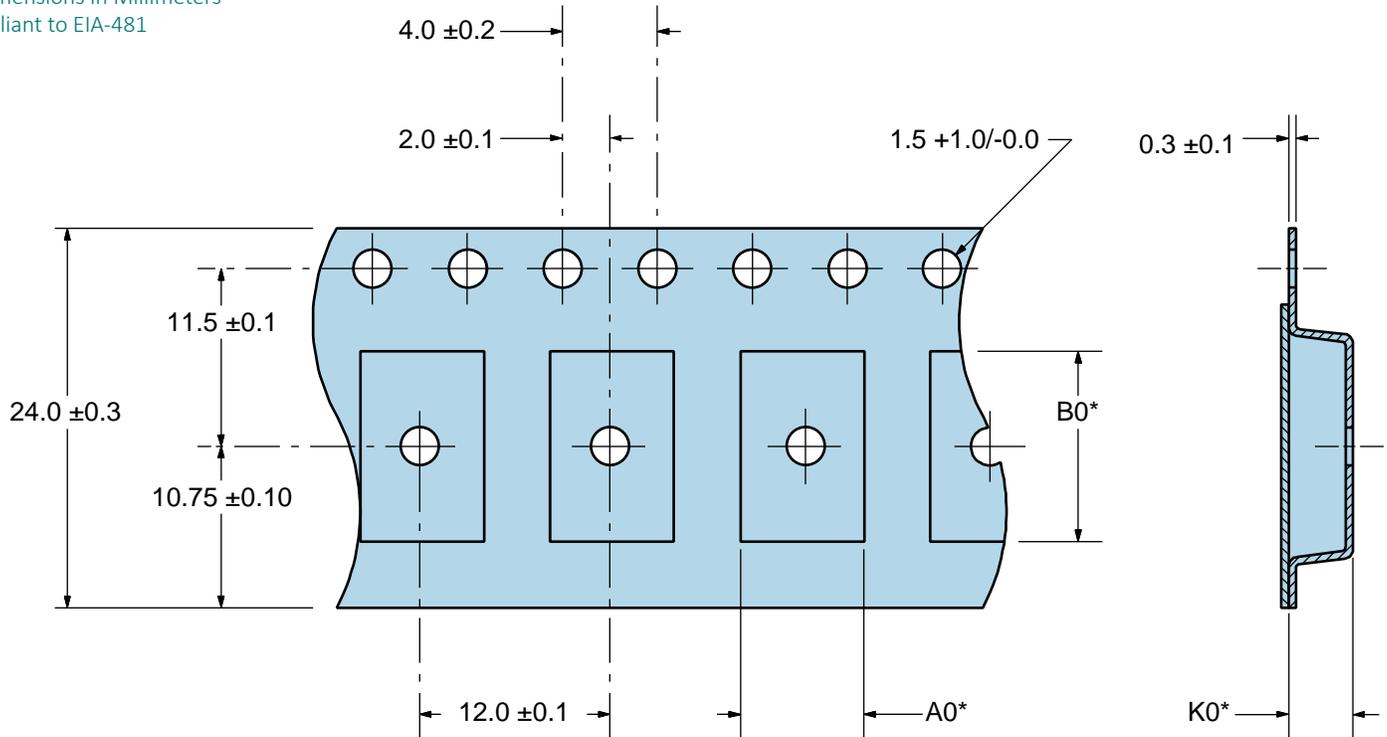
EH1445SJETS-6.720M TR

Tape & Reel Dimensions

Quantity Per Reel: 1,000 units

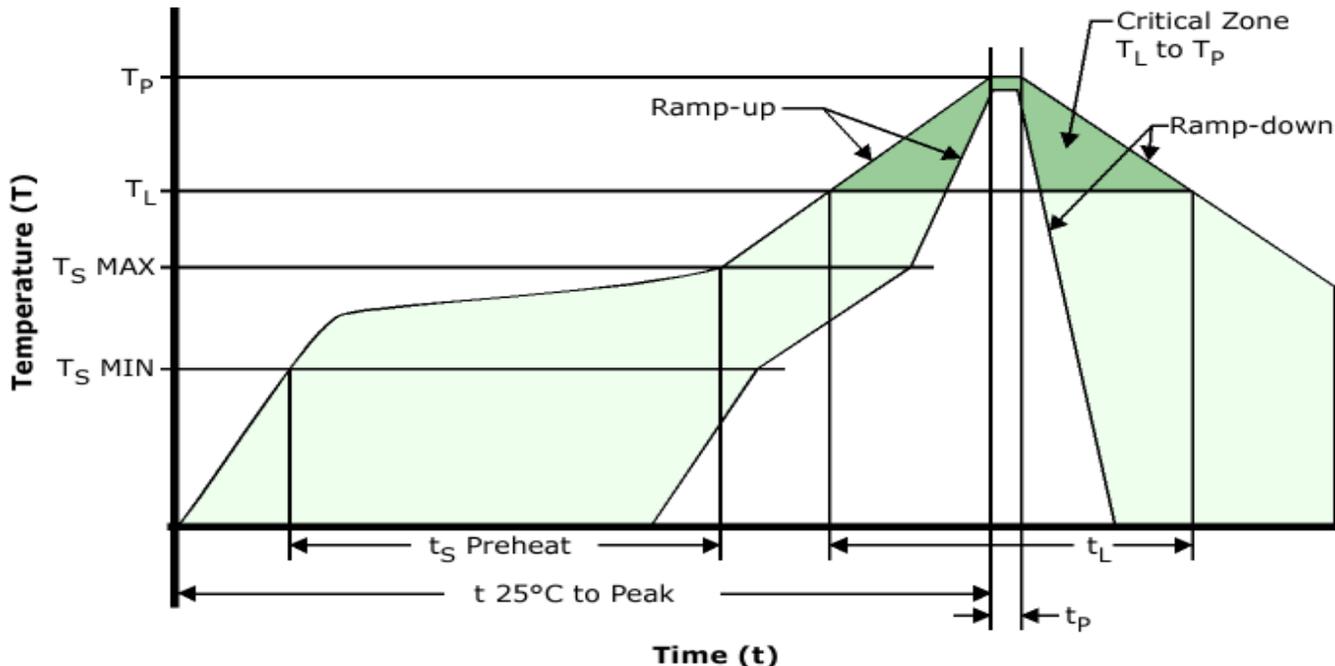
All Dimensions in Millimeters

Compliant to EIA-481



EH1445SJETS-6.720M TR

Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T_S MAX to T_L (Ramp-up Rate) 5°C/Second Maximum

Preheat

- Temperature Minimum (T_S MIN) N/A
 - Temperature Typical (T_S TYP) 150°C
 - Temperature Maximum (T_S MAX) N/A
 - Time (t_s MIN) 60 - 120 Seconds

Ramp-up Rate (T_L to T_P) 5°C/Second Maximum

Time Maintained Above:

- Temperature (T_L) 150°C
 - Time (t_L) 200 Seconds Maximum

Peak Temperature (T_P) 240°C Maximum

Target Peak Temperature (T_P Target) 240°C Maximum 2 Times / 230°C Maximum 1 Time

Time within 5°C of actual peak (t_p) 10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature (t) N/A

Moisture Sensitivity Level Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum.